

TO-3P Plastic-Encapsulate Transistors

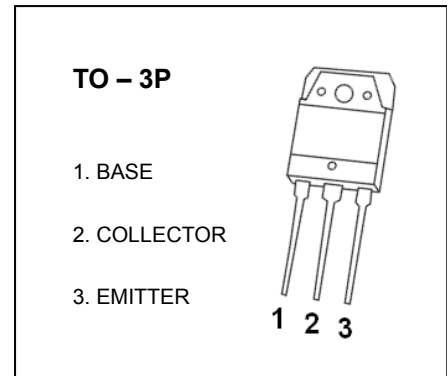
3DA5200B TRANSISTOR (NPN)

FEATURES

- High Breakdown Voltage
- High Current and Power Capacity

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	15	A
P_C	Collector Power Dissipation	3	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	42	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=50\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=160\text{V}, I_E=0$			5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=1\text{A}$	55		160	
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=7\text{A}$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=8\text{A}, I_B=800\text{mA}$			3	V
Base-emitter voltage	V_{BE}	$V_{CE}=5\text{V}, I_C=7\text{A}$			1.5	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		360		pF
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=1\text{A}$		30		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	R	O
RANGE	55-110	80-160